	Application No.	Applicant(s)
Notice of Allowability	10/691,843	CHEN ET AL.
	Examiner	Art Unit
	David S. Blum	2813
The MAILING DATE of this communication apperature All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT R of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in this ap or other appropriate communication IGHTS. This application is subject t	plication. If not included n will be mailed in due course. THIS
1. This communication is responsive to		
2. The allowed claim(s) is/are <u>18-32</u> .		
3. The drawings filed on 26 February 2004 are accepted by t	he Examiner.	
 4. Acknowledgment is made of a claim for foreign priority unally all b) Some* c) None of the: 1. Certified copies of the priority documents have 2. Certified copies of the priority documents have 3. Copies of the certified copies of the priority documents have 1. Certified copies of the priority documents have 2. Certified copies of the certified copies of the priority documents have 3. Copies of the certified copies of the priority documents have 1. Certified copies not received: 	e been received. e been received in Application No cuments have been received in this of this communication to file a reply MENT of this application. hitted. Note the attached EXAMINER es reason(s) why the oath or declara st be submitted. son's Patent Drawing Review (PTO- c. s Amendment / Comment or in the (1.84(c)) should be written on the drawithe header according to 37 CFR 1.121(sit of BIOLOGICAL MATERIAL I	national stage application from the complying with the requirements as AMENDMENT or NOTICE OF ation is deficient. 1948) attached Office action of the back) of the complying with the front (not the back) of the complying in the submitted. Note the
Attachment(s) 1. ☑ Notice of References Cited (PTO-892) 2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948) 3. ☑ Information Disclosure Statements (PTO-1449 or PTO/SB/C Paper No./Mail Date 7/30/04 / 10/23/03 4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material	6. ⊠ Interview Summary Paper No./Mail Da 08), 7. ⊠ Examiner's Amendo	te <u>2/28/05</u> .

This action is in response to the application filed 10/23/03.

EXAMINER'S AMENDMENT

1. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview with Yingsheng Tung on 2/28/05.

The application has been amended as follows:

Cancel claims 1-17.

Reasons for Allowance

- 2. Claims 18-32 are allowed.
- 3. The following is an examiner's statement of reasons for allowance:

Claim 18 limits the formation of a trench structure to having a trench formed in a semiconductor layer where the top surface of the layer has an oxidation rate that is lower than that of other major crystallographic planes of the semiconductor material. This limitation, in combination with the other limitations of claim 18 is not taught or suggested by the prior art of record. Wolf (page 448), Ishitsuka (US006284625B1), and Olsen (US006150234A) teach a standard structure where a silicon nitride mask is used

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in forming the trench. The silicon nitride oxidizes at a slower rate than the silicon substrate (Ishitsuka and Olsen refer to the silicon nitride layer as an oxidation inhibition film), but is not a top surface of the semiconductor layer, but rather a layer formed above the semiconductor layer. Peters (Choices and Challenges for Shallow Trench Isolation) also teaches the conventional practice of Wolf but does not teach or suggest a top surface within the semiconductor layer that has a slower oxidation rate. Bannerjee (US006707132B1) forms a SiGe layer at the top surface of the silicon substrate (the instant application uses germanium to alter the oxidation characteristics of the silicon layer), but the silicon germanium layer at the surface is formed in trenches rather than forming trenches through the silicon germanium layer as in the instant claims. Theodore forms a strained silicon layer (also silicon –germanium) at the surface of a silicon layer, but implants through the layer to form a conductive region rather than forming an opening through the layer.

Claims 19-32 are allowed as being properly dependent upon allowed claim 18.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

4. Any inquiry concerning this communication or earlier communications from the examiner should be directed to David S. Blum whose telephone number is (571)-272-1687) and e-mail address is David.blum@USPTO.gov.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl Whitehead Jr., can be reached at (571)-272-1702. Our facsimile number all patent correspondence to be entered into an application is (703) 872-9306. The facsimile number for customer service is (703)-872-9317.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

David S. Blum

February 28, 2005